CORRECTED VERSION OF THE SPECIFICATION

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The invention relates to fabrication of integrated circuit devices incorporating different thicknesses of gate oxides by using nitrogen implantation. Either angled nitrogen implantation or nitride spacers are used to create a "shadow effect", which limits the nitrogen dose close to the edges of the active area. This reduction of nitrogen dose leads to an increased gate oxide thickness at the active area adjacent to the shallow trench and increases the threshold of the parasitic corner device and reduces sub Vt (threshold voltage) and junction leakage.

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FIG. 1 is a graph comparing thickness reduction factor versus level of nitrogen dosage by implantation for a 800°C dry oxidation in pure oxygen.

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